



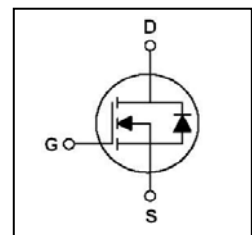
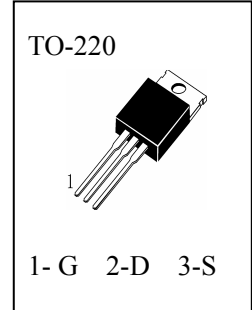
N-Channel Enhancement Mode Field Effect Transistor

■ Applications

- Servo motor control.
- Power MOSFET gate drivers.
- DC/DC converters
- Other switching applications.

■ Features

- 75A, 80V(See Note), $R_{DS(on)} < 13mV\Omega @ V_{GS} = 10V$
- Fast switching
- 100% avalanche tested
- Minimize input capacitance and gate charge
- Equivalent Type:ME75N80C



■ Maximum Ratings (Ta=25°C unless otherwise specified)

T_{stg}	Storage Temperature	-----	-55~150°C
T_j	Operating Junction Temperature	-----	150°C
V_{DSS}	Drain-Source Voltage	-----	80V
V_{GSS}	Gate-Source Voltage	-----	±20V
I_D	Drain Current (Continuous)($T_c=25^\circ C$)	-----	75A
I_{DM}	Pulsed Drain Current (Note 1)	-----	300A
P_D	Maximum Power Dissipation ($T_c=25^\circ C$)	-----	75W
	($T_A=25^\circ C$)	-----	4W
E_{AS}	Pulsed Avalanche Energy (Note 2)	-----	400mJ

■ Thermal Characteristics

Symbol	Items	TO-220	Unit
Rthj-case	Thermal Resistance Junction-case	Max 2.0	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max 62.5	°C/W

**Electrical Characteristics** (Ta=25°C unless otherwise specified)

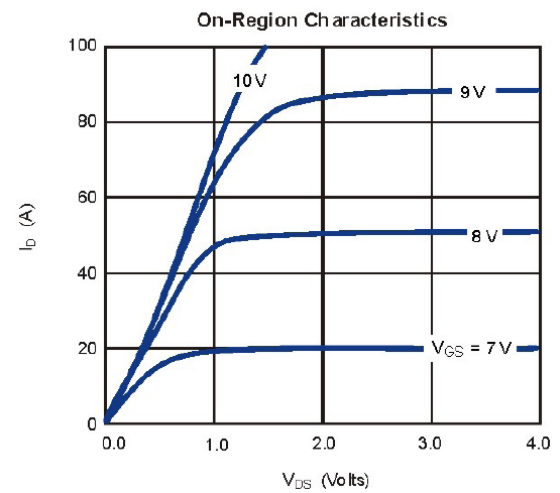
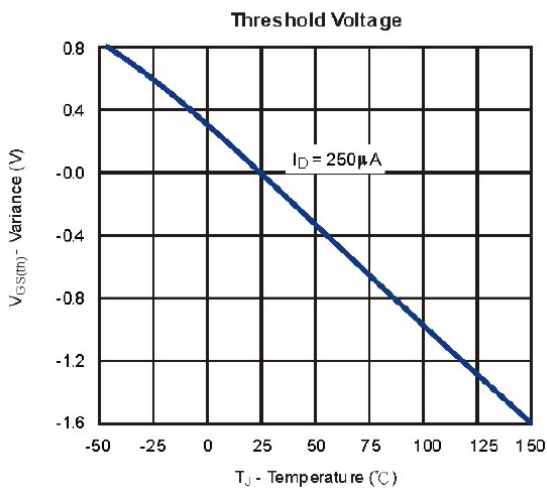
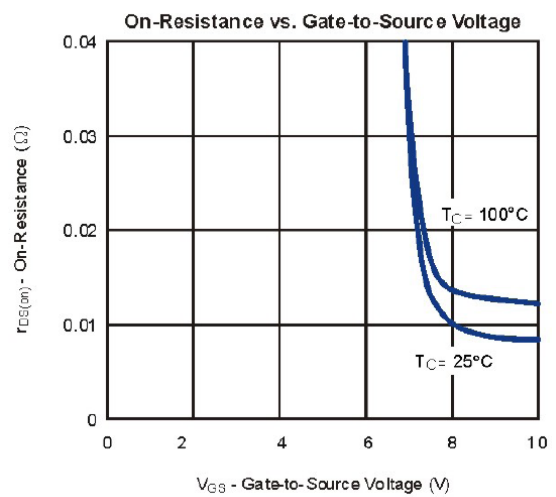
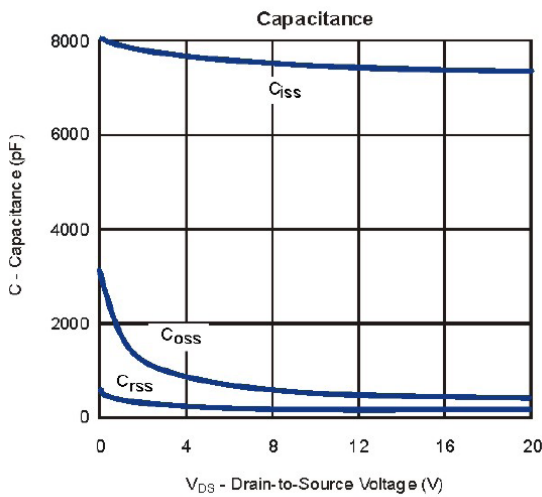
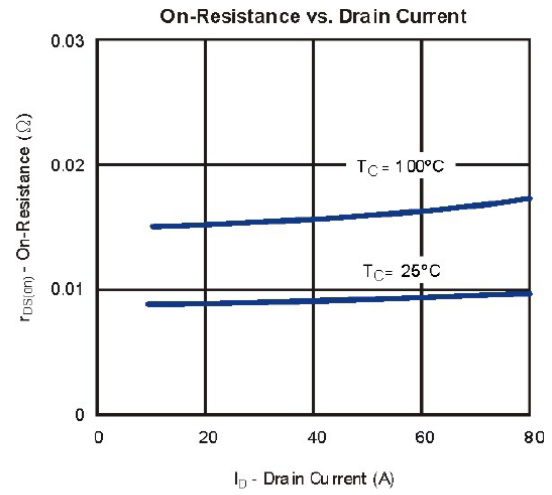
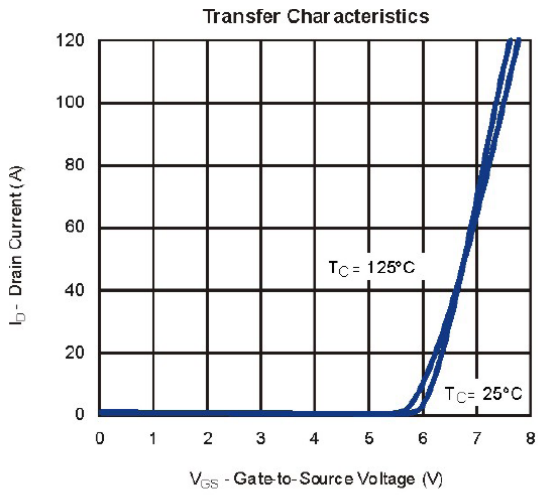
Symbol	Items	Min.	Typ.	Max.	Unit	Conditions
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	80			V	I _D =250μA, V _{GS} =0V
I _{DSS}	Zero Gate Voltage Drain Current			1	μA	V _{DS} =80V, V _{GS} =0V
I _{GSS}	Gate – Body Leakage			±100	nA	V _{GS} = ±20V, V _{DS} =0V
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	4.0		6.5	V	V _{DS} = V _{GS} , I _D =250μA
R _{DS(on)}	Static Drain-Source On-Resistance			13	mΩ	V _{GS} =10V, I _D =40A (Note 3)
Dynamic Characteristics and Switching Characteristics						
C _{iss}	Input Capacitance		7400		pF	V _{DS} = 20 V, V _{GS} = 0V, f = 1.0 MHz
C _{oss}	Output Capacitance		450		pF	
C _{rss}	Reverse Transfer Capacitance		140		pF	
t _{d(on)}	Turn - On Delay Time		80		nS	V _{DS} = 30V, V _{GS} = 10 V, R _L =15 Ω, R _G = 10 Ω (Note 3)
t _r	Rise Time		37		nS	
t _{d(off)}	Turn - Off Delay Time		140		nS	
t _f	Fall Time		27		nS	
Q _g	Total Gate Charge		120		nC	V _{DS} =60V, I _D =75A, V _{GS} = 10V (Note 3)
Q _{gs}	Gate–Source Charge		54		nC	
Q _{gd}	Gate–Drain Charge		38		nC	
R _g	Gate Resistance		2.3		Ω	f=1MHz
Drain-Source Diode Characteristics and Maximun Ratings						
I _S	Continuous Source–Drain Diode Forward Current			75	A	
I _{SM}	Pulsed Drain-Source Diode Forward Current			300	A	
V _{SD}	Source–Drain Diode Forward On–Voltage			1.5	V	I _S =25A, V _{GS} =0(Note 3)

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_D=30A, V_{DD}=37.5V, Starting T_J=25°C
3. Pulse Test: Pulse width≤300μS, Duty Cycle≤2%

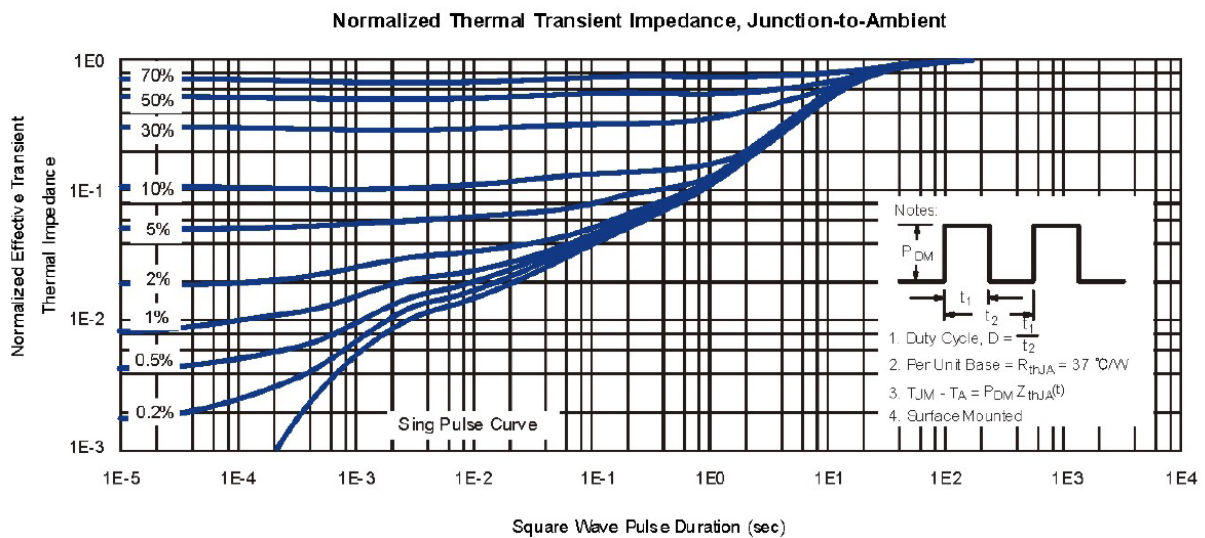
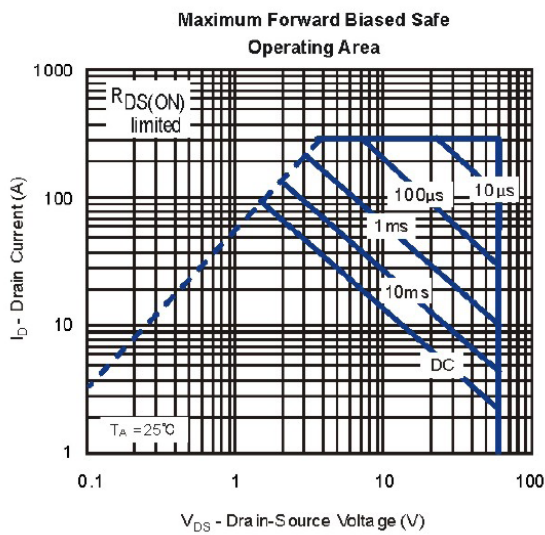
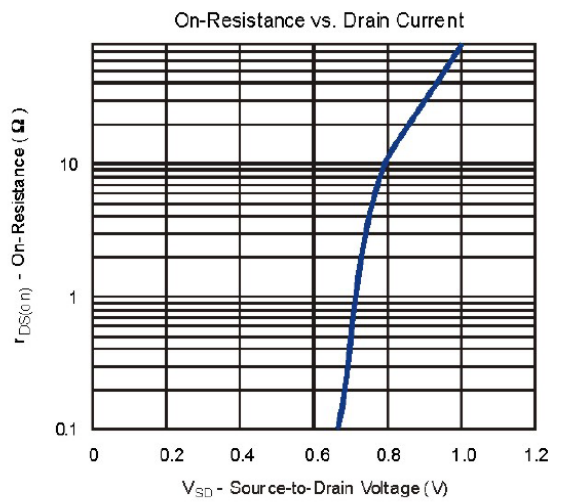
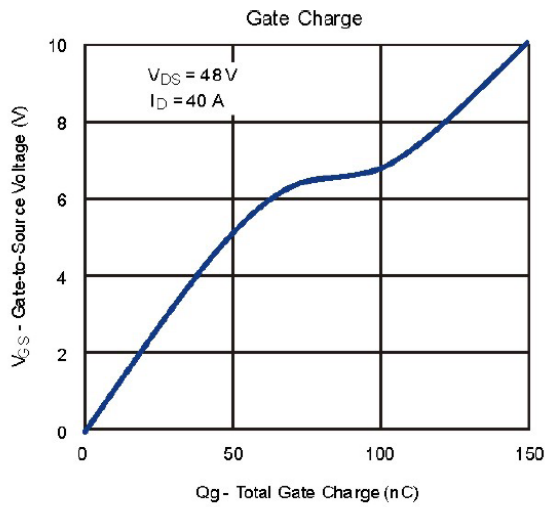


Typical Characteristics





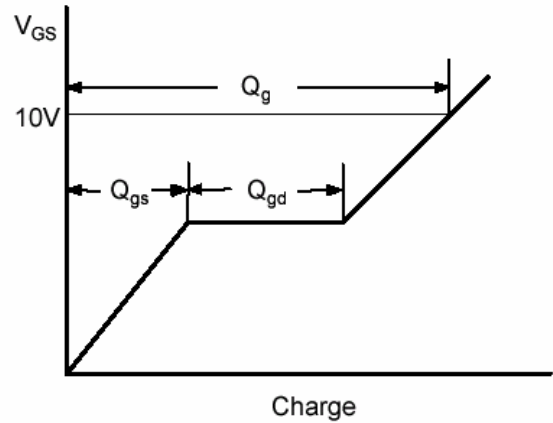
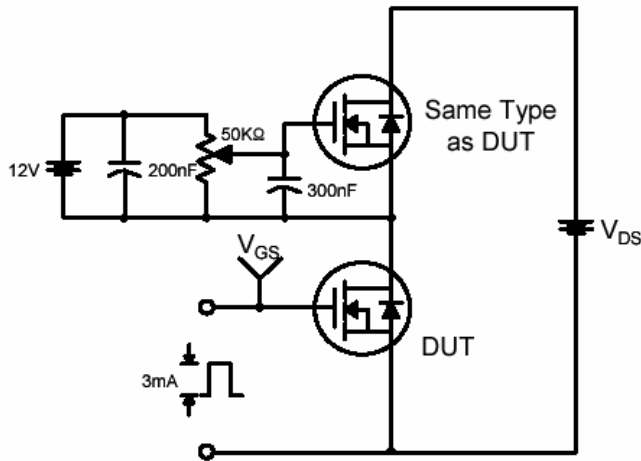
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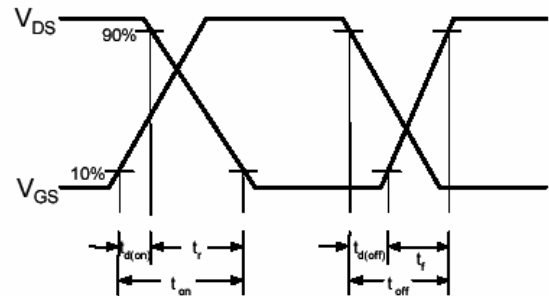
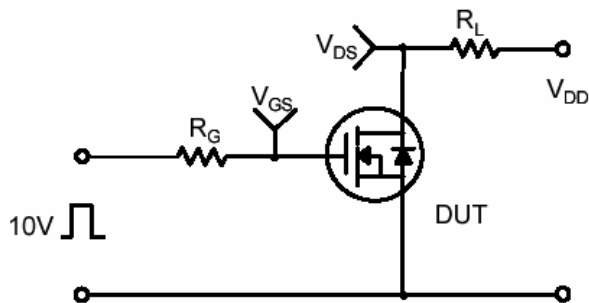


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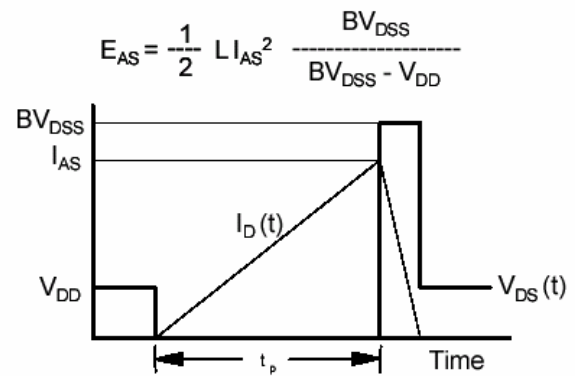
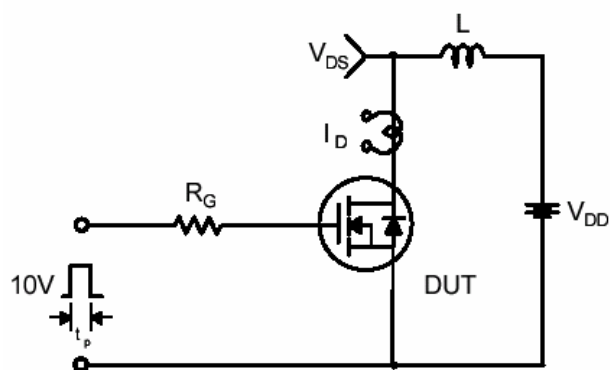
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms





■ Typical Characteristics

Peak Diode Recovery dv/dt Test Circuit & Waveforms

